L Number	Hits	Search Text	DB	Time stamp
1	136444	gate with (dielectric insulat\$3)	USPAT;	2004/07/28 09:26
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
2	13824	(ozone oxygen) near2 radical	USPAT;	2004/07/28 09:35
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
3	5803887	@ad>19990428 @RLAD>19990428	USPAT;	2004/07/28 09:35
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
4	4433	(oxidation oxidating oxidizing oxidization) same (nitriding	USPAT;	2004/07/28 09:59
		nitridating nitridation)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
5	138283	silicon with nitride	USPAT;	2004/07/28 09:35
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_			IBM_TDB	
6	4489	post with anneal\$3	USPAT;	2004/07/28 09:35
			US-PGPUB;	
i			EPO; JPO;	
		*	DERWENT;	
_		Maridakia adalahan adalahan sadalahan sadalahan birah	IBM_TDB	2004/07/20 00:25
7	28	((oxidation oxidating oxidizing oxidization) same (nitriding	USPAT;	2004/07/28 09:36
		nitridating nitridation)) same (post with anneal\$3)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
8	25	(gate with (dielectric insulat\$3)) same ((ozone oxygen) near2	IBM_TDB USPAT;	2004/07/28 09:59
0	25	radical) same (oxidation oxidating oxidizing oxidization)	US-PGPUB;	2007/07/20 05.35
		radical) same (oxidation oxidating oxidizing oxidization)	EPO; JPO;	
			DERWENT;	
.			IBM_TDB	
ا وا	47	(((gate with (dielectric insulat\$3)) same ((oxidation oxidating	USPAT;	2004/07/28 10:08
	"	oxidizing oxidization) same (nitriding nitridating nitridation)))	US-PGPUB;	200 1/07/20 10:00
		same (silicon with nitride)) not (@ad>19990428	EPO; JPO;	
		@RLAD>19990428)	DERWENT;	
			IBM_TDB	